

Silicon NPN Power Transistors

2SC4747

DESCRIPTION

- With TO-3PFM package
- High speed switching
- High breakdown voltage

APPLICATIONS

- Character display horizontal deflection output

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

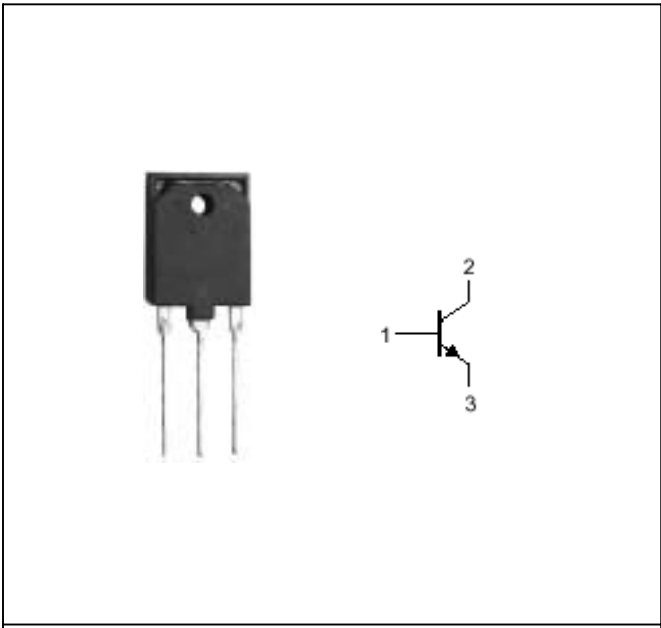


Fig.1 simplified outline (TO-3PFM) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		10	A
I _{C(surge)}	Collector current-surge		20	A
P _C	Collector power dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon NPN Power Transistors**2SC4747****CHARACTERISTICS**T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; R _{BE} =0	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA ; I _C =0	6			V
I _{CES}	Collector cut-off current	V _{CE} =1500V; R _{BE} =0			0.5	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	8		30	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =8A ; I _B =1.6A			5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =8A ; I _B =1.6A			1.5	V
t _f	Fall time	I _{CP} =7A; I _{B1} =1.4A			0.3	μs

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PACKAGE OUTLINE

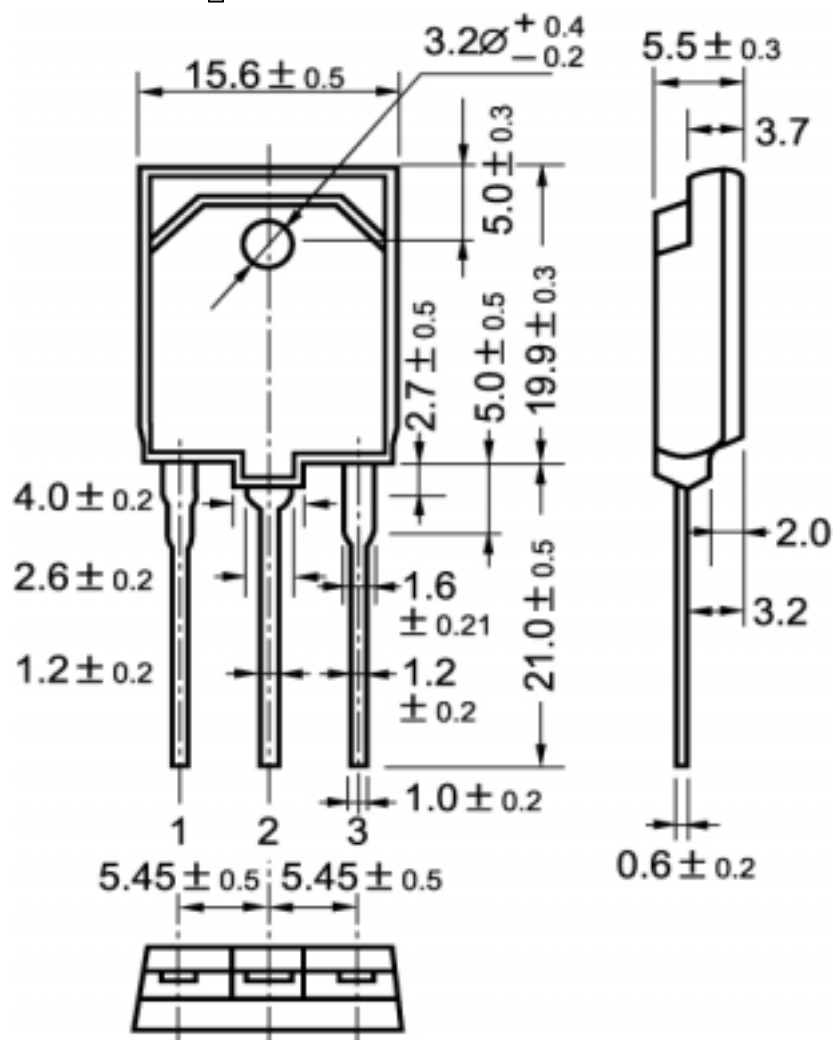


Fig.2 outline dimensions